

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method for fabricating a semiconductor film comprising:
irradiating a semiconductor film formed over a substrate with a laser beam to crystallize the semiconductor film,
wherein ultrasonic vibration is applied to the substrate during irradiating the laser beam while holding an end portion of the substrate.
2. (Original) A method for fabricating a semiconductor film according to claim 1, wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.
3. (Original) A method for fabricating a semiconductor film comprising:
holding a substrate over a stage having pores wherein said substrate is provided with a semiconductor film;
spouting gases from the pores to float the substrate; and
irradiating a semiconductor film formed over the substrate with a laser beam while holding an end portion of the substrate,
wherein during irradiating the laser beam, ultrasonic vibration is applied to the substrate.
4. (Original) A method for fabricating a semiconductor film according to claim 3, wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.
5. (Original) A method for fabricating a semiconductor device comprising:

forming a semiconductor film having an amorphous structure over a substrate; and

irradiating the semiconductor film with a laser beam while applying ultrasonic vibration to the substrate to crystallize the semiconductor film.

6. (Original) A method for fabricating a semiconductor device according to claim 5,

wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

7. (Original) A method for fabricating a semiconductor device according to claim 5,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

8. (Original) A method for fabricating a semiconductor device comprising:
forming a semiconductor film having an amorphous structure over a substrate; and

irradiating the semiconductor film with a laser beam condensed into a linear shape in an oxygen atmosphere while floating the substrate and applying ultrasonic vibration to the substrate to crystallize the semiconductor film.

9. (Original) A method for fabricating a semiconductor device according to claim 8,

wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

10. (Original) A method for fabricating a semiconductor device according to claim 8,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

11. (Original) A method for fabricating a semiconductor device comprising:
forming a semiconductor film having an amorphous structure over a substrate;
irradiating the semiconductor film with a laser beam condensed into a linear shape while applying ultrasonic vibration to the substrate to crystallize the semiconductor film; and
crystallizing a whole surface of the semiconductor film while overlapping a beam spot of the laser beam on the film.

12. (Original) A method for fabricating a semiconductor device according to claim 11,

wherein said laser beam is a YVO_4 , a YAG, a YLF or an excimer laser.

13. (Original) A method for fabricating a semiconductor device according to claim 11,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

14. (Original) A method for fabricating a semiconductor device comprising:
forming a semiconductor film having an amorphous structure over a substrate;

crystallizing the semiconductor film having an amorphous structure by adding a metal element or a metal compound having catalytic action for enhancing a crystallization of the semiconductor film and by heat-treating; and

irradiating the semiconductor film with a laser beam condensed into a linear shape while floating the substrate and applying ultrasonic vibration to the substrate in order to improve a crystallinity of the semiconductor film.

15. (Original) A method for fabricating a semiconductor device according to claim 14,

wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

16. (Original) A method for fabricating a semiconductor device according to claim 14,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

17. (Original) A method for fabricating a semiconductor device according to claim 14,

wherein said metal element is nickel or platinum.

18. (Original) A method for fabricating a semiconductor device comprising:
forming a semiconductor film having an amorphous structure over a substrate;
crystallizing the semiconductor film having the amorphous structure by adding a metal element or a metal compound having catalytic action for enhancing a crystallization of the semiconductor film and by heat-treating;

irradiating the semiconductor film with a laser beam condensed into a linear beam while applying ultrasonic vibration to the substrate in order to improve a crystallinity of the semiconductor film; and

improving a crystallinity of the semiconductor film while overlapping a beam spot of the laser beam on the film.

19. (Original) A method for fabricating a semiconductor device according to claim 18,

wherein said laser beam is a YVO_4 , a YAG, a YLF or an excimer laser.

20. (Original) A method for fabricating a semiconductor device according to claim 18,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

21. (Original) A method for fabricating a semiconductor device according to claim 18,

wherein said metal element is nickel or platinum.

22.-25. (Canceled)